NEC

MOS FIELD EFFECT TRANSISTOR

μPA652TT

P-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

The μPA652TT is a switching device, which can be driven directly by a 2.5 V power source.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

FEATURES

- 2.5 V drive available
- Low on-state resistance
  $R_{DS(on)1}$ = 294 mΩ MAX. (V_{GS} = –4.5 V, I_D = –1.0 A)
  $R_{DS(on)2}$ = 336 mΩ MAX. (V_{GS} = –4.0 V, I_D = –1.0 A)
  $R_{DS(on)3}$ = 514 mΩ MAX. (V_{GS} = –2.5 V, I_D = –0.5 A)

ORDERING INFORMATION

PART NUMBER	PACKAGE
μPA652TT	6pinWSOF (1620)

Marking: WF

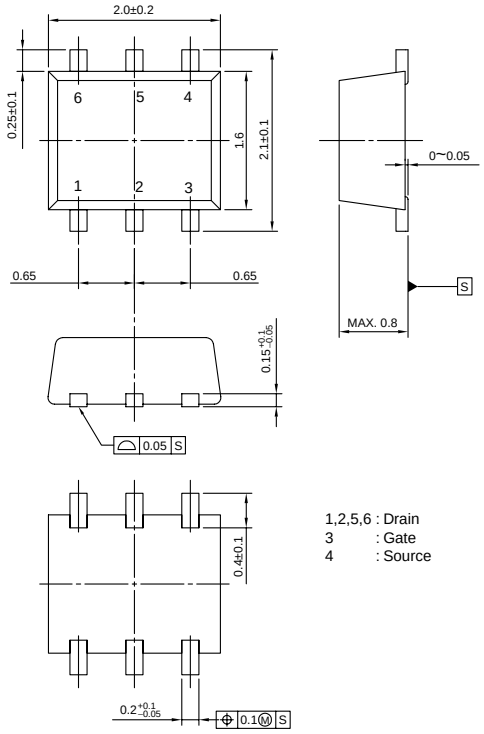
ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage (V_{GS} = 0 V)	V_{DSS}	–20	V
Gate to Source Voltage (V_{DS} = 0 V)	V_{GSS}	∓12	V
Drain Current (DC)	$I_{D(DC)}$	∓2.0	A
Drain Current (pulse) Note1	$I_{D(pulse)}$	∓8.0	A
Total Power Dissipation	P_{T1}	0.2	W
Total Power Dissipation Note2	P_{T2}	1.3	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature	T_{stg}	–55 to +150	°C

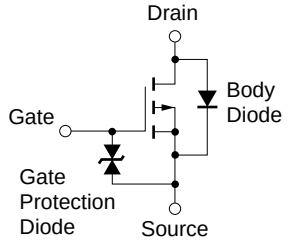
Notes 1. PW ≤ 10 μs, Duty Cycle ≤ 1%

2. Mounted on FR-4 board of 5000 mm² x 1.1 mm, t ≤ 5 sec.

PACKAGE DRAWING (Unit: mm)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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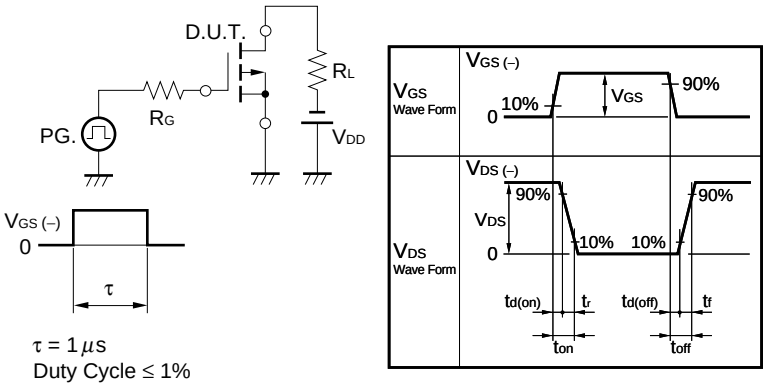
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

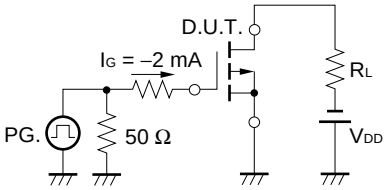
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = –20 V, V_{GS} = 0 V			–10	μA
Gate Leakage Current	I_{GSS}	V_{GS} = ∓12 V, V_{DS} = 0 V			∓10	μA
Gate Cut-off Voltage	$V_{GS(off)}$	V_{DS} = –10 V, I_D = –250 μA	–0.5	–1.1	–1.5	V
Forward Transfer Admittance	$\|y_{fs}\|$	V_{DS} = –10 V, I_D = –1.0 A	1.0	2.4		S
Drain to Source On-state Resistance	$R_{DS(on)1}$	V_{GS} = –4.5 V, I_D = –1.0 A		235	294	mΩ
	$R_{DS(on)2}$	V_{GS} = –4.0 V, I_D = –1.0 A		252	336	mΩ
	$R_{DS(on)3}$	V_{GS} = –2.5 V, I_D = –0.5 A		385	514	mΩ
Input Capacitance	C_{iss}	V_{DS} = –10 V		126		pF
Output Capacitance	C_{oss}	V_{GS} = 0 V		47		pF
Reverse Transfer Capacitance	C_{rss}	f = 1.0 MHz		17		pF
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = –10 V, I_D = –1.0 A		28		ns
Rise Time	t_r	V_{GS} = –4.0 V		101		ns
Turn-off Delay Time	$t_{d(off)}$	R_G = 10 Ω		80		ns
Fall Time	t_f			85		ns
Total Gate Charge	Q_G	V_{DD} = –16 V		1.1		nC
Gate to Source Charge	Q_{GS}	V_{GS} = –4.0 V		0.4		nC
Gate to Drain Charge	Q_{GD}	I_D = –2.0 A		0.5		nC
Body Diode Forward Voltage	$V_{F(S-D)}$	I_F = 2.0 A, V_{GS} = 0 V		0.93		V

TEST CIRCUIT 1 SWITCHING TIME



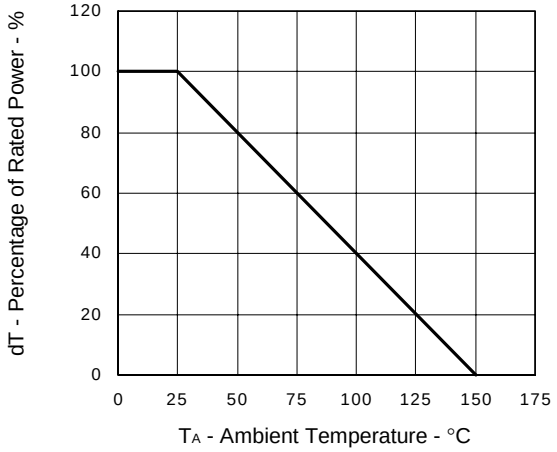
τ = 1 μs
Duty Cycle ≤ 1%

TEST CIRCUIT 2 GATE CHARGE

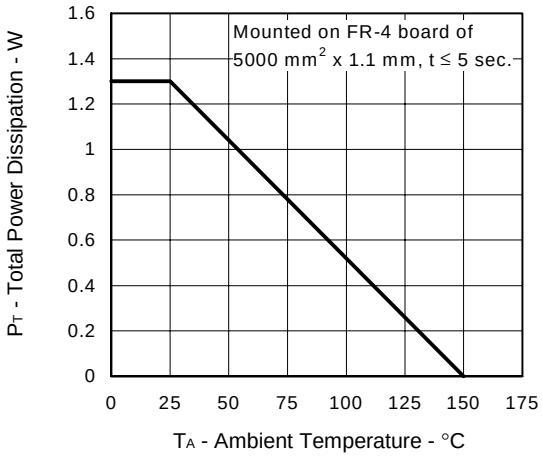


TYPICAL CHARACTERISTICS (T_A = 25°C)

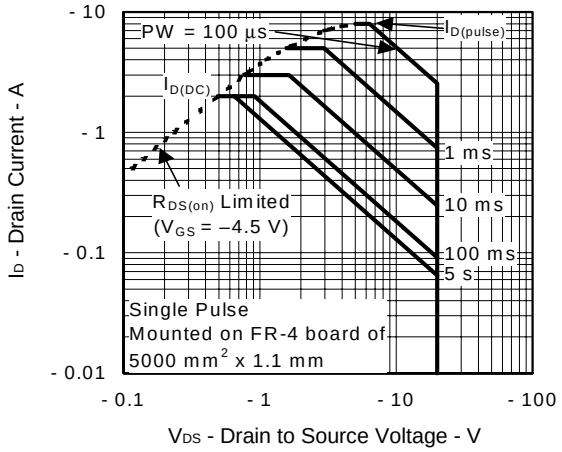
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



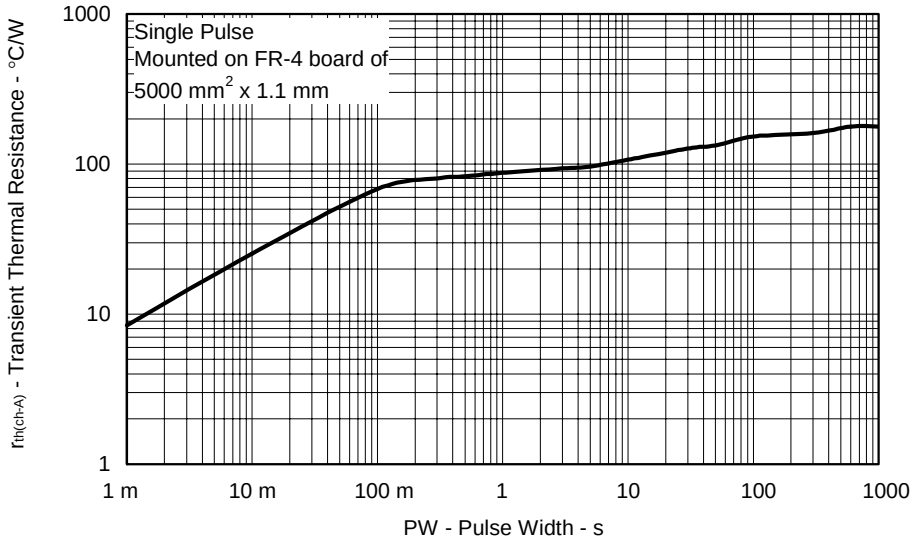
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



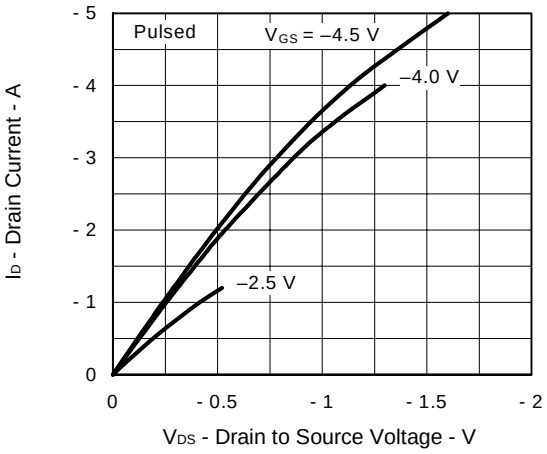
FORWARD BIAS SAFE OPERATING AREA



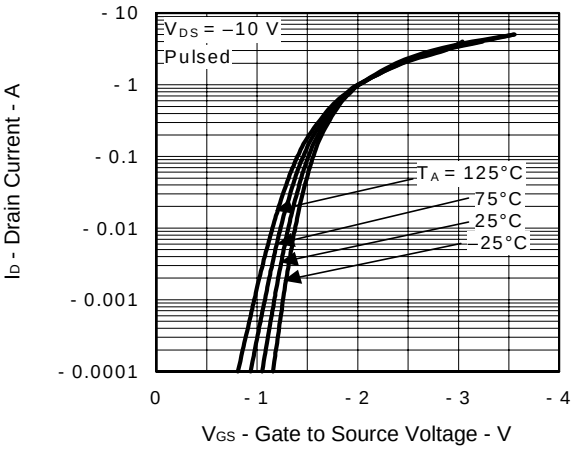
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



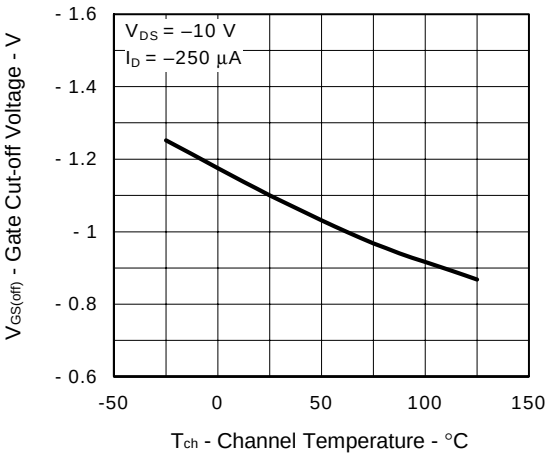
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



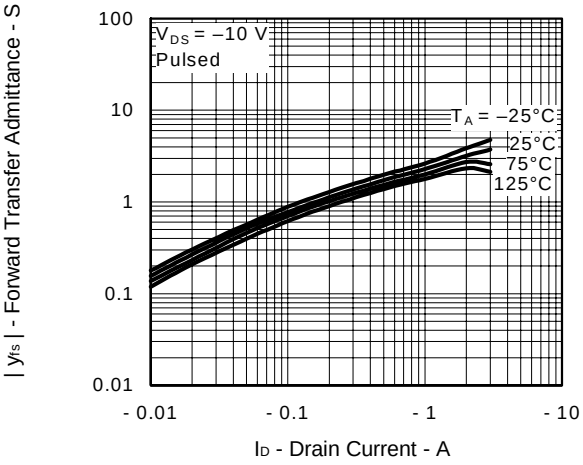
FORWARD TRANSFER CHARACTERISTICS



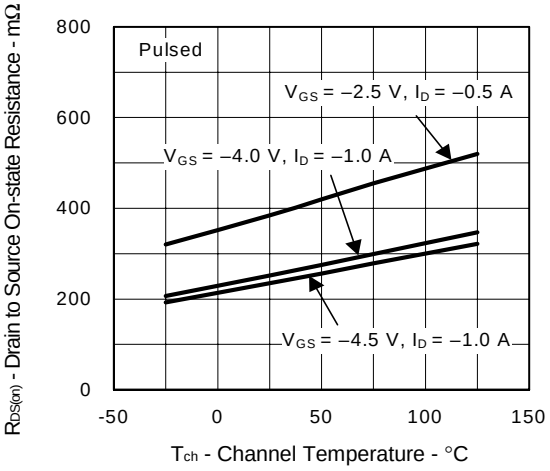
GATE CUT-OFF VOLTAGE vs.
CHANNEL TEMPERATURE



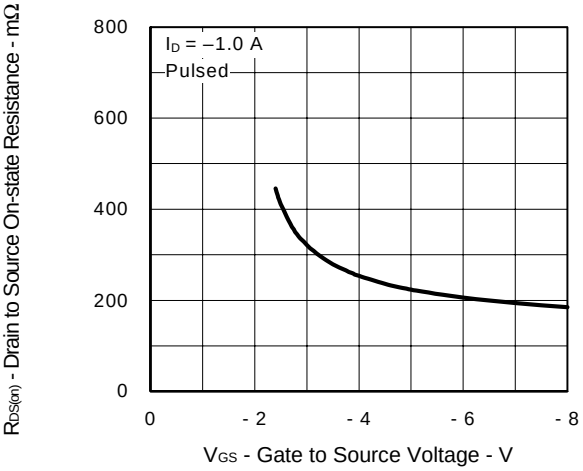
FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT



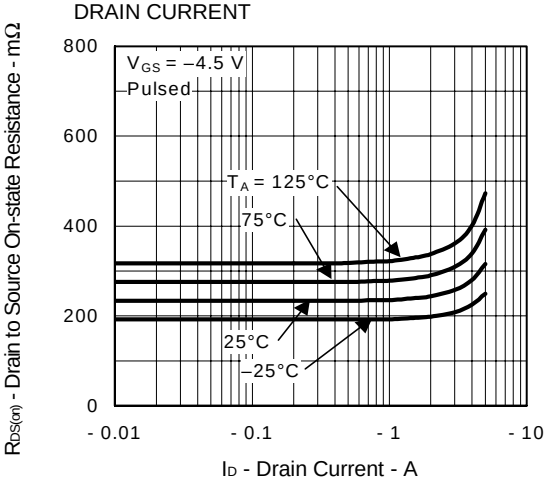
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
CHANNEL TEMPERATURE



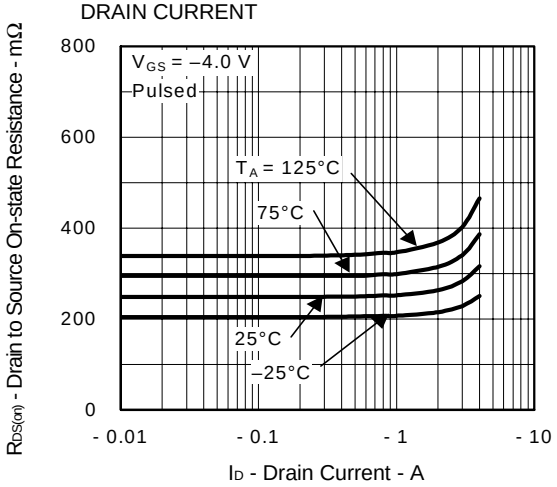
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE



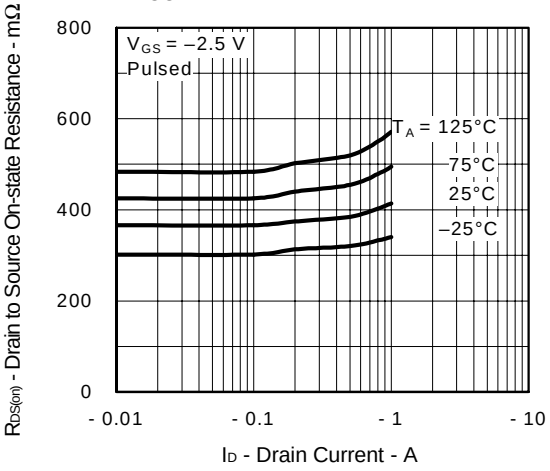
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



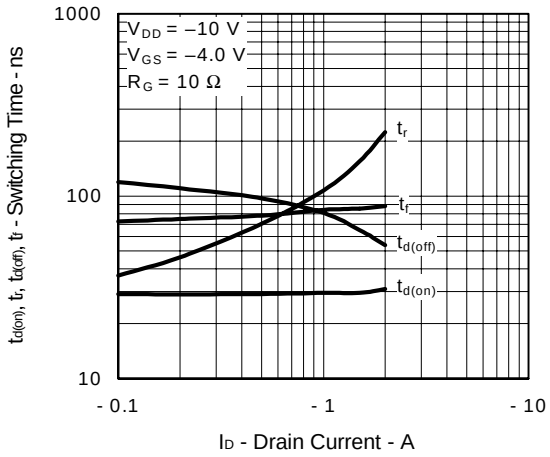
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



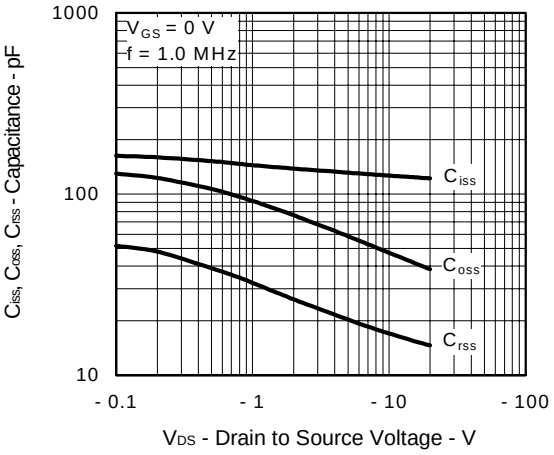
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



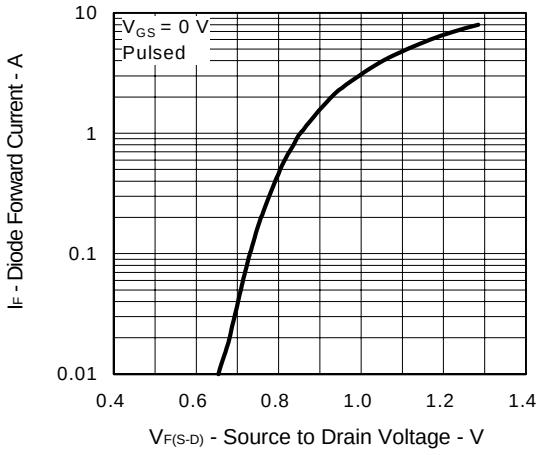
SWITCHING CHARACTERISTICS



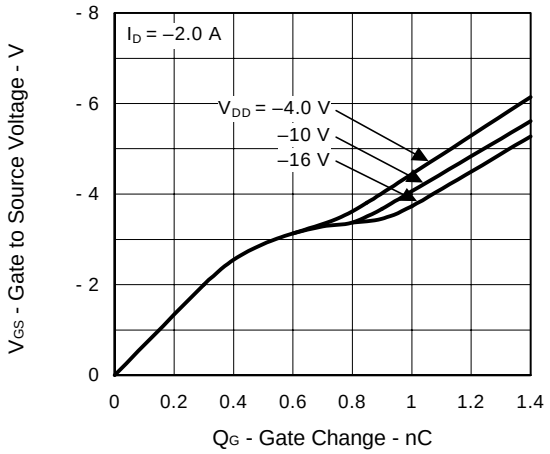
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



DYNAMIC INPUT/OUTPUT CHARACTERISTICS



[MEMO]

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